

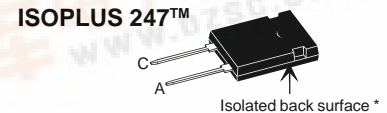
IXYS DSEP 30-06CR

HiPerDynFRED™ Epitaxial Diode with soft recovery (Electrically Isolated Back Surface)

I_{FAV} = 30 A
V_{RRM} = 600 V
t_{rr} = 20 ns

Preliminary Data

V _{RSM} V	V _{RRM} V	Type
600	600	DSEP 30-06CR



A = Anode, C = Cathode

* Patent pending

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		70	A
I _{FAVM}	T _C = 135°C; rectangular, d = 0.5	30	A
I _{FRM}	t _p < 10 μs; rep. rating, pulse width limited by T _{VJM}	tbd	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	300	A
E _{AS}	T _{VJ} = 25°C; non-repetitive I _{AS} = 3 A; L = 180 μH	1.2	mJ
I _{AR}	V _A = 1.5·V _R typ.; f = 10 kHz; repetitive	0.3	A
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	250	W
V _{ISOL}	50/60 Hz RMS; I _{ISOL} ≤ 1 mA	2500	V~
F _C	mounting force with clip	20...120	N
Weight	typical	6	g

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low cathode to tab capacitance (<25pF)
- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM}	250	μA
	T _{VJ} = 150°C V _R = V _{RRM}	1	mA
V _F ②	I _F = 30 A; T _{VJ} = 150°C T _{VJ} = 25°C	1.79	V
		2.46	V
R _{thJC}	with heatsink compound	0.6	K/W
R _{thCH}		0.25	K/W
t _{rr}	I _F = 1 A; -di/dt = 200 A/μs; V _R = 30 V; T _{VJ} = 25°C	20	ns
I _{RM}	V _R = 100 V; I _F = 50 A; -di _F /dt = 100 A/μs T _{VJ} = 100°C	4.5	7.0 A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
 ② Pulse Width = 300 μs, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

Dimensions see outlines.pdf